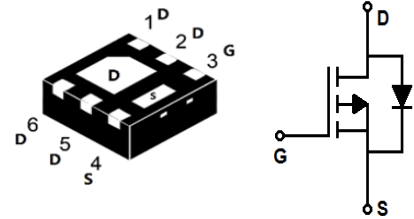


-30V/-9A P-Channel MOSFET

$V_{(BR)DSS}$	$R_{DS(ON)}$ Typ	I_D Max
-30V	18mΩ @-10V	-9A
	26mΩ @ -4.5V	

DFN2X2-6L

Features

- Low $R_{DS(on)}$ @ $V_{GS} = -10V$
- -5V Logic Level Control
- 100% UIS Tested
- Pb-Free, RoHS Compliant

Applications

- Load Switch
- Switching circuits
- High Speed Line Drive
- Power Management Functions

Order Information

Product	Package	Marking	Packing
M03P09P	DFN2X2-6L	P3009G	3000PCS/Reel

Absolute Maximum Ratings

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

Symbol	Parameter	Rating	Unit	
Common Ratings (T _A =25°C Unless Otherwise Noted)				
V _{GS}	Gate-Source Voltage	±20	V	
V _{(BR)DSS}	Drain-Source Breakdown Voltage	-30	V	
T _J	Maximum Junction Temperature	175	°C	
T _{STG}	Storage Temperature Range	-50 to 150	°C	
Mounted on Large Heat Sink				
I _{DM}	Pulse Drain Current Tested①	T _C =25°C	-125	A
I _D	Continuous Drain Current	T _C =25°C	-9	A
		T _C =70°C	-7.2	
P _D	Maximum Power Dissipation	T _C =25°C	26	W
		T _C =70°C	20	
EAS	Avalanche energy, single pulsed ②		43	mJ
R _{θJc}	Thermal Resistance-Junction to ambient		3	°C/W

-30V/-9A P-Channel MOSFET

Symbol	Parameter	Condition	Min	Typ	Max	Unit
Static Electrical Characteristics @ T _J = 25°C (unless otherwise stated)						
V _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V I _D =-250μA	-30	--	--	V
I _{DSS}	Zero Gate Voltage Drain Current(T _A =25°C)	V _{DS} =-30V, V _{GS} =0V	--	--	-1	μA
	Zero Gate Voltage Drain Current(T _A =125°C)	V _{DS} =-24V, V _{GS} =0V	--	--	-100	uA
I _{GSS}	Gate-Body Leakage Current	V _{GS} =±20V, V _{DS} =0V	--	--	±100	nA
V _{GS(TH)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =-250μA	-1.2	-1.6	-2.5	V
R _{DS(ON)}	Drain-Source On-State Resistance③	V _{GS} =-10V, I _D =-8A	--	18	25	mΩ
R _{DS(ON)}	Drain-Source On-State Resistance③	V _{GS} =-4.5V, I _D =-5A	--	26	35	mΩ
Dynamic Electrical Characteristics @ T _J = 25°C (unless otherwise stated)						
C _{iss}	Input Capacitance	V _{DS} =-15V, V _{GS} =0V, f=1MHz	--	1140	--	pF
C _{oss}	Output Capacitance		--	170	--	pF
C _{rss}	Reverse Transfer Capacitance		--	130	--	pF
R _g	Gate Resistance	f=1MHz		23		Ω
Q _g	Total Gate Charge	V _{DS} =-15V I _D =-5A, V _{GS} =-10V	--	21.4	--	nC
Q _{gs}	Gate Source Charge		--	3	--	nC
Q _{gd}	Gate Drain Charge		--	4.8	--	nC
Switching Characteristics @ T _J = 25°C (unless otherwise stated)						
t _{d(on)}	Turn on Delay Time	V _{DD} =-15V, I _D =-1A, R _G =3.3Ω, V _{GS} =-10V	--	8.2	--	ns
t _r	Turn on Rise Time		--	9.8	--	ns
t _{d(off)}	Turn Off Delay Time		-	15	--	ns
t _f	Turn Off Fall Time		--	8.5	--	ns
Source Drain Diode Characteristics						
I _{SD}	Source drain current(Body Diode)	T _J =25°C	--	--	-9	A
V _{SD}	Forward on voltage③	T _J =25°C, I _{SD} =-3A, V _{GS} =0V	--	-0.85	-1.2	V

Notes: ① Pulse width limited by maximum allowable junction temperature

② Pulse width ≤ 300μs; duty cycles ≤ 2%.

-30V/-9A P-Channel MOSFET

Typical Characteristics

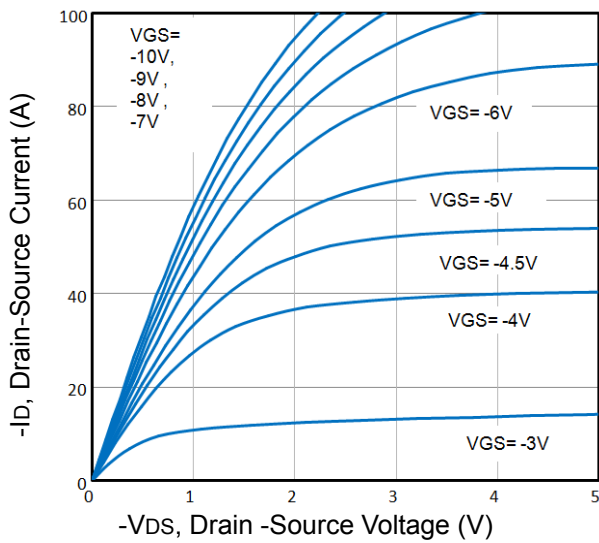


Fig1. Typical Output Characteristics

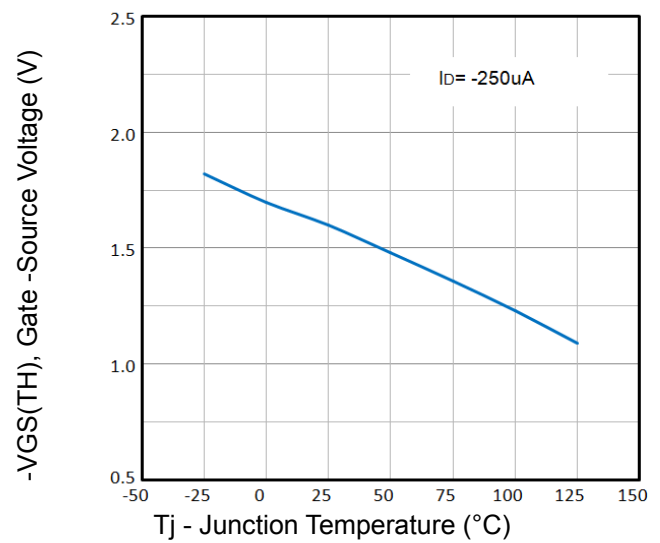


Fig2. Normalized Threshold Voltage Vs. Temperature

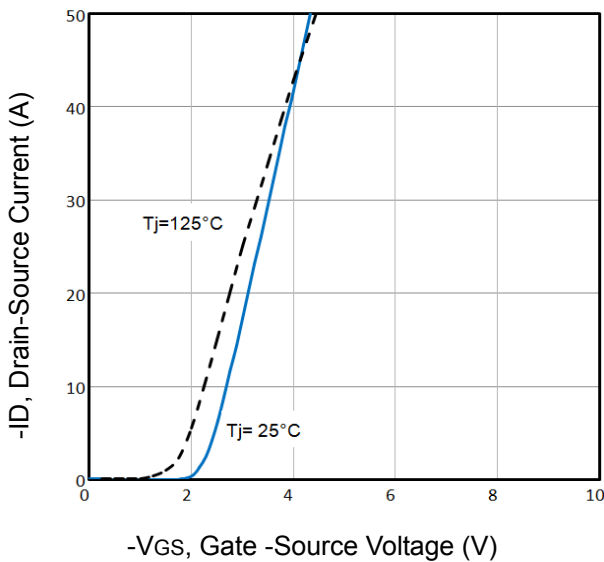


Fig3. Typical Transfer Characteristics

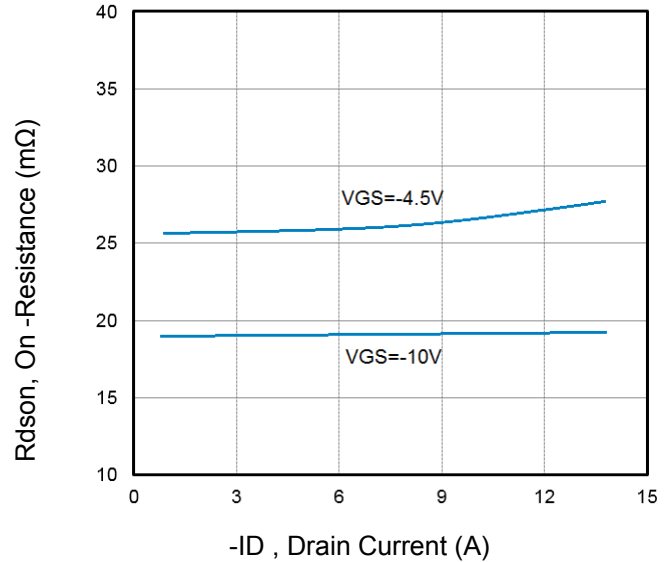


Fig4. On-Resistance vs. Drain Current and Gate

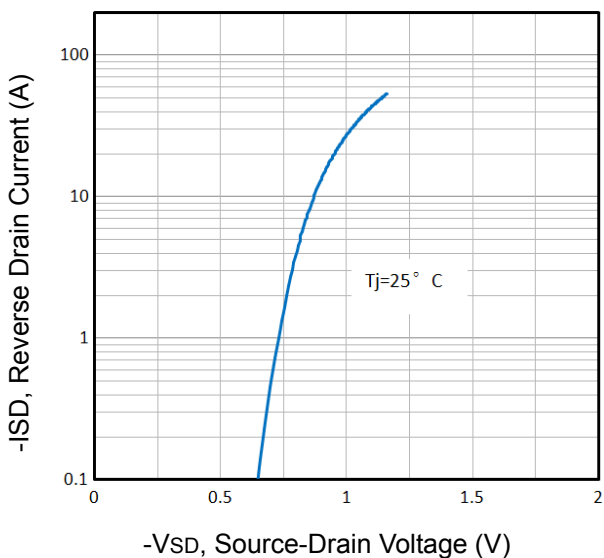


Fig5. Typical Source-Drain Diode Forward Voltage

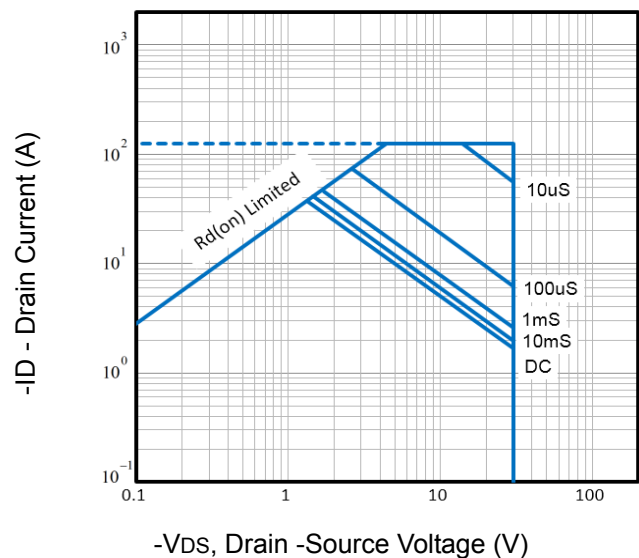


Fig6. Maximum Safe Operating Area

-30V/-9A P-Channel MOSFET

Typical Characteristics

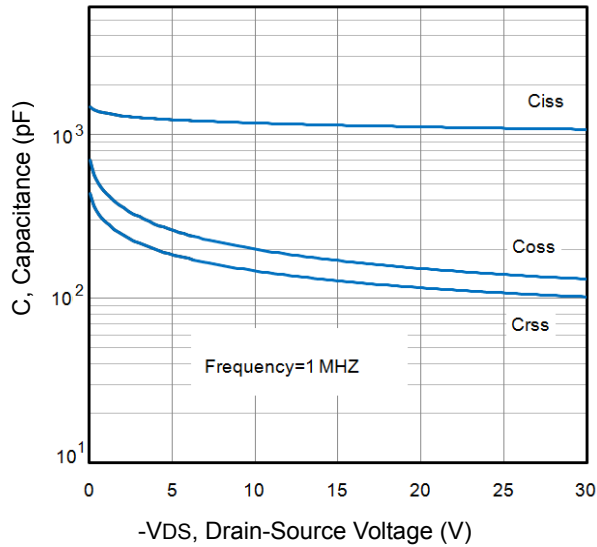


Fig7. Typical Capacitance Vs. Drain-Source Voltage

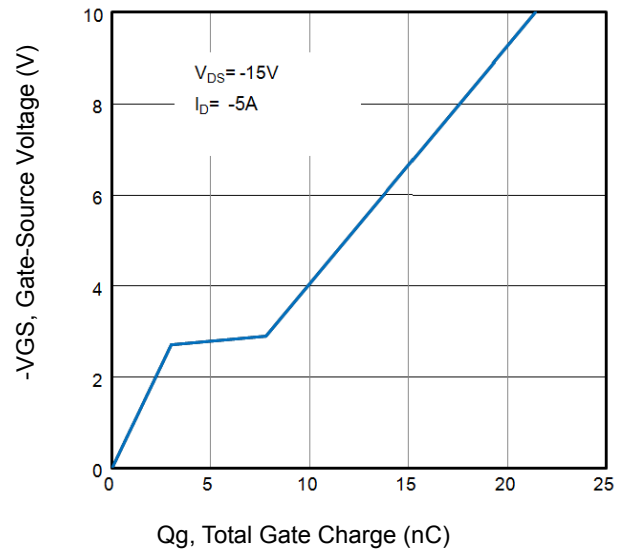


Fig8. Typical Gate Charge Vs. Gate-Source Voltage

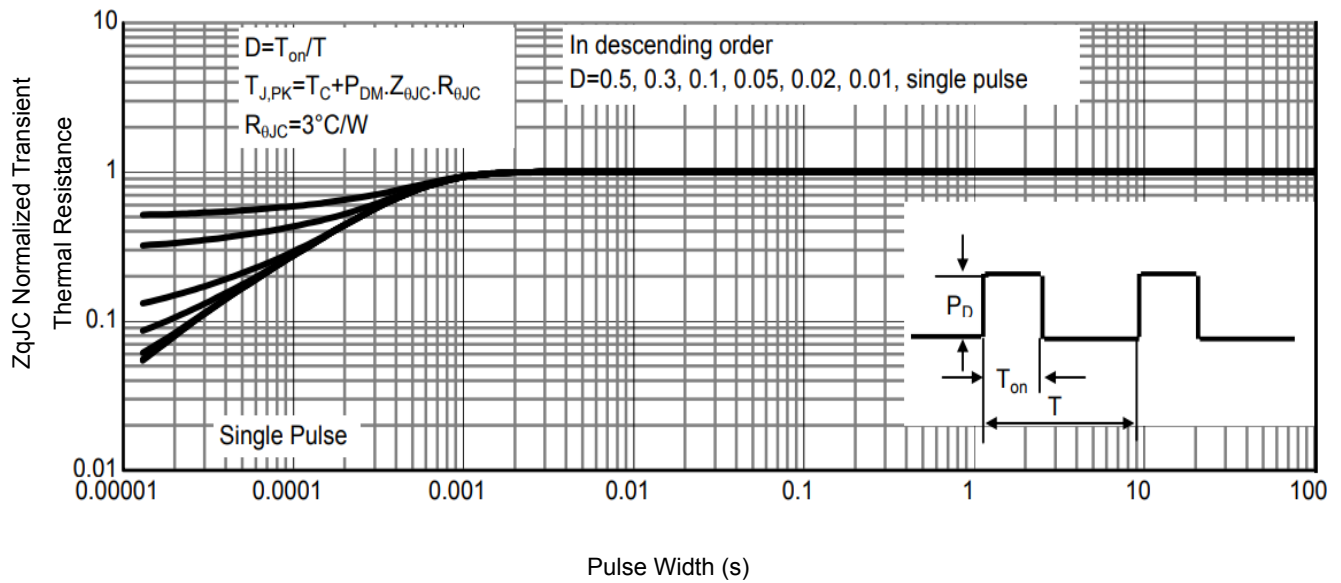


Fig9. Normalized Maximum Transient Thermal Impedance

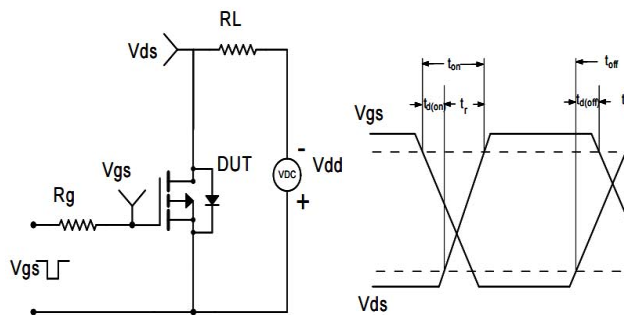


Fig10. Switching Time Test Circuit and waveforms

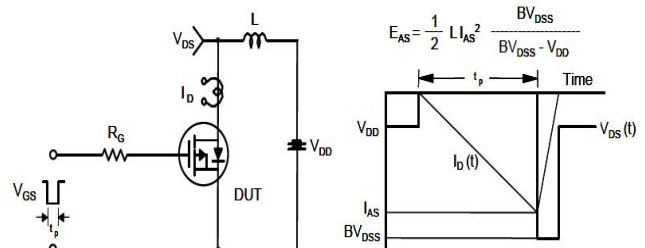
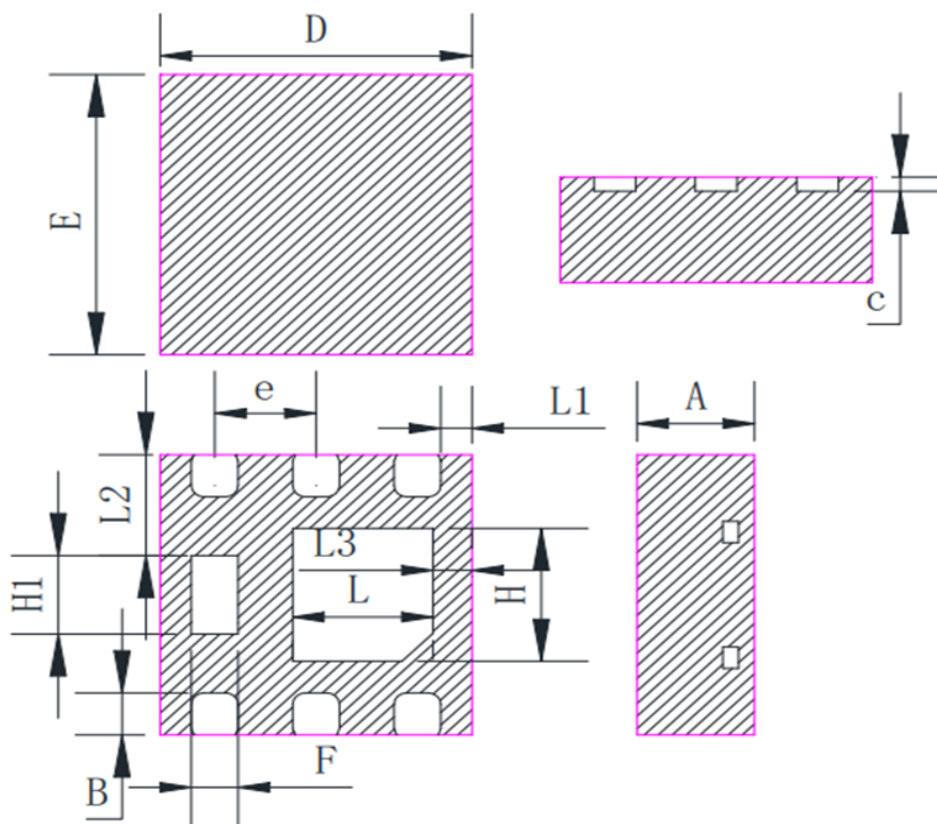


Fig11. Unclamped Inductive Test Circuit and waveforms

-30V/-9A P-Channel MOSFET

DFN2X2-6L Mechanical Data



DIMENSIONS (unit : mm)

Symbol	Min	Typ	Max
A	0.70	0.75	0.80
B	0.25	0.30	0.35
C	0.153	0.203	0.253
D	1.90	2.00	2.10
E	1.90	2.00	2.10
e	0.60	0.65	0.70
F	0.25	0.30	0.35
H	0.85	0.95	1.05
H1	0.51	0.56	0.61
L	0.80	0.90	1.00
L1	0.15	0.20	0.25
L2	0.62	0.72	0.82
L3	0.25	0.30	0.35